Hierarchical ternary Ni-Co-Se nanowires for High-Performance Supercapacitor Device Design

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Determination of the weight of active material: The mass of NiSe on NF was calculated by a common difference method as follows. After the reaction, the weight increment (x mg) of NF can be directly measured by electronic balance. NiSe_{loading}=x mg×(M_{NiSe}/M_{Se})=x mg×(138/79)=1.7x mg, where M is the molecular weight or atomic weight. For the content of active material in the exchanged samples, according to our previous work, we have confirmed that the residual NF does not participate in the Co ion exchange reaction. Therefore, the weight of active material for the Co-exchanged samples is the difference of weight between Co-exchanged samples and the residual metal nickel obtained by the above calculations. For the fabricated Ni@Ni-Co-Se//AC ASCs, the active material loading of all the products is about 12 mg cm⁻², which is more conducive to the practical application.



Figure S1. CV curves of (a) Ni@NiSe, (b) Ni@Ni_{0.8}Co_{0.2}Se, (c) Ni@Ni_{0.6}Co_{0.4}Se and (d) Ni@Co₉Se₈ at different scan rates from 10 mV s⁻¹ to 50 mV s⁻¹ in a three-electrode system.



Figure S2. (a) CV curves of AC at different scan rates from 10 mV s⁻¹ to 50 mV s⁻¹. (b) CV curves of Ni@NiSe and AC electrodes measured at a scan rate of 10 mV s⁻¹ in a three-electrode system.

Sample Element	<u>Ni@</u> NiSe	Ni@Ni _{0.8} Co _{0.2} Se	Ni@Ni _{0.6} Co _{0.4} Se	Ni@Co ₉ Se ₈
Ni	49.67	47.74	35.02	13.38
Co	-	10.49	21.36	45.46
Se	50.33	41.77	43.61	41.16

Table S1. The results of EDX from Ni@NiSe, Ni@Ni $_{0.8}$ Co $_{0.2}$ Se, Ni@Ni $_{0.6}$ Co $_{0.4}$ Se and Ni@Co $_{9}$ Se $_{8}$.

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Table S2. The detailed data of energy density and power density of Ni@NiSe,Ni@Ni_8Co_2Se, Ni@Ni_6Co_4Se and Ni@Co_8SeNi@Co_8Co_2Se, Ni@Ni_6Co_4Se and Ni@Co_8Se

	Data							
Ni@NiSe	E (Wh/kg)	18.8	17.0	16.8	13.1	11.5	10.3	9.5
	P (W/kg)	37.7	57.1	96.3	197.2	410.9	628.7	1032.3
Ni@Ni _{0.8} Co _{0.2} Se	E (Wh/kg)	32.1	31.2	29.8	26.9	23.7	20.6	17.0
	P (W/kg)	37.9	57.4	96.8	200.3	444.9	721.1	1526.8
Ni@Ni _{0.6} Co _{0.4} Se	E (Wh/kg)	20.9	19.8	14.0	12.2	11.4	10.2	9.4
	P (W/kg)	37.7	56.8	95.1	193.6	392.9	612.1	1062.9
Ni@Co ₉ Se ₈	E (Wh/kg)	22.9	22.4	22.2	20.6	19.4	18.6	16.9
	P (W/kg)	38.1	57.6	98.9	203.7	449.0	768.3	1685.1

Device	Specific capacitance	Energy density	Power density	Mass loading of positive electrode	Source
Ni _{0.67} Co _{0.33} Se//RGO	176 C g ⁻¹ (1 A g ⁻¹)	36.7 Wh Kg ⁻	750 W kg ⁻¹	2.5 mg cm ⁻²	J. Mater. Chem. A, 2015 ,3, 23653-23659
Ni _{0.9} Co _{1.92} Se ₄ //AC	80 F g ⁻¹ (2 mA cm ⁻²)	26.29 Wh Kg ⁻	265 W kg ⁻¹	-	RSC Adv., 2016 ,6, 75251- 75257
(Ni,Co) _{0.85} Se// graphene film	529.3 mF cm ⁻² (1 mA cm ⁻²)	2.85 mWh cm ⁻³	10.76 mW cm ⁻³	5.63 mg cm ⁻²	Nano Energy 24 (2016) 78–86
Co _{0.85} Se//AC	0.33 F cm ⁻² (1 mA cm ⁻²)	$\frac{6 \times 10^{-5}}{\text{Wh cm}^{-2}}$	-	1.35 mg cm ⁻²	ACS Appl. Mater. Interfaces 2014 , 6, 18844–18852
Ni _{0.85} Se//AC	92.9 F g ⁻¹ (1 A g ⁻¹)	32.2 Wh Kg ⁻	789.6 W kg ⁻¹	1.2 mg cm ⁻²	RSC Adv., 2015 , 5, 81474–81481
La ₂ Se ₃ //graphite	8.13 F g ⁻¹ (5 mV s ⁻¹)	1.6 Wh kg ⁻¹	960 W kg ⁻¹	-	ChemPlusChem 2015 , 80, 1478– 1487
Ni _{0.8} Co _{0.2} Se//AC	86 F g ⁻¹ (1 A g ⁻¹)	32.1 Wh kg ⁻ 1	37.9 W kg ⁻¹	12 mg cm⁻ ₂	Our work

Table S3. the comparison on the electrochemical performance of our $Ni@Ni_{0.8}Co_{0.2}Se//AC$ asymmetric device with other metal-selenide-based ASC devices from literature.